

Amendments to the Abstract:

Please replace the current Abstract with the following new Abstract:

Abstract

A method for manufacturing an SiCOI composite substrate is disclosed. For one embodiment an initial substrate comprising an SiC support bearing a layer of SiO₂ whereon a thin layer of SiC is transferred is supplied. For one such embodiment, the thin layer of SiC is a 6H or 4H polytype SiC. An epitaxy of SiC on the thin layer of SiC is conducted at a temperature from 1450°C to obtain 6H or 4H polytype epitaxy on the transferred thin 6H or 4H polytype layer respectively.